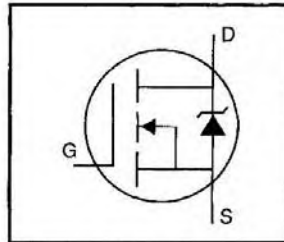


HEXFET® Power MOSFET

**IRLR110PbF**  
**IRLU110PbF**

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Surface Mount (IRLR110)
- Straight Lead (IRLU110)
- Available in Tape & Reel
- Logic-Level Gate Drive
- R<sub>DS(on)</sub> Specified at V<sub>GS</sub>=4V & 5V
- Lead-Free

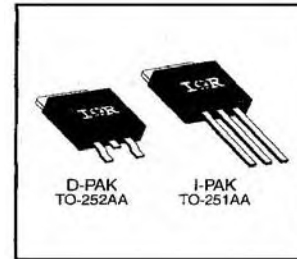


$V_{DSS} = 100V$   
 $R_{DS(on)} = 0.54\Omega$   
 $I_D = 4.3A$

**Description**

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, V <sub>GS</sub> @ 5.0 V	4.3	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, V <sub>GS</sub> @ 5.0 V	2.7	
$I_{DM}$	Pulsed Drain Current ①	17	W
$P_D @ T_C = 25^\circ C$	Power Dissipation	25	
$P_D @ T_A = 25^\circ C$	Power Dissipation (PCB Mount)**	2.5	W/°C
	Linear Derating Factor	0.20	
	Linear Derating Factor (PCB Mount)**	0.020	
V <sub>GS</sub>	Gate-to-Source Voltage	±10	V
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	100	mJ
I <sub>AR</sub>	Avalanche Current ①	4.3	A
E <sub>AR</sub>	Repetitive Avalanche Energy ①	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	260 (1.6mm from case)	

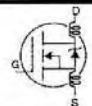
**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	—	5.0	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (PCB mount)**	—	—	50	
R <sub>θJA</sub>	Junction-to-Ambient	—	—	110	

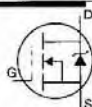
\*\* When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

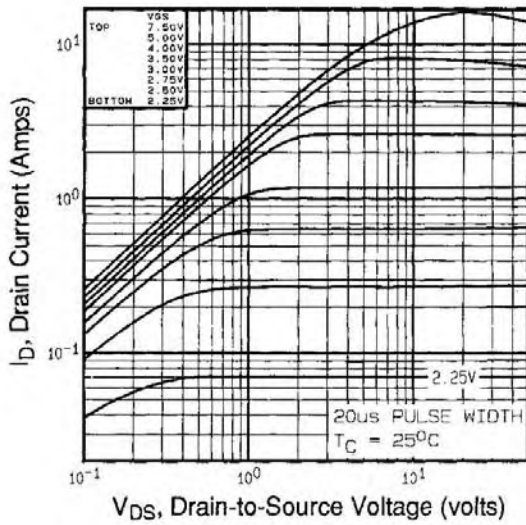
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.12	—	V/°C	Reference to $25^\circ\text{C}, I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.54	$\Omega$	$V_{GS}=5.0V, I_D=2.6A$ ③
		—	—	0.76		$V_{GS}=4.0V, I_D=2.2A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$g_{fs}$	Forward Transconductance	2.3	—	—	S	$V_{DS}=50V, I_D=2.6A$ ④
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS}=100V, V_{GS}=0V$
		—	—	250		$V_{DS}=80V, V_{GS}=0V, T_J=125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=10V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-10V$
$Q_g$	Total Gate Charge	—	—	6.1	nC	$I_D=5.6A$
$Q_{gs}$	Gate-to-Source Charge	—	—	2.0		$V_{DS}=80V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	3.3		$V_{GS}=5.0V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	9.3	—	ns	$V_{DD}=50V$
$t_r$	Rise Time	—	47	—		$I_D=5.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	16	—		$R_G=12\Omega$
$t_f$	Fall Time	—	17	—		$R_D=8.4\Omega$ See Figure 10 ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact 
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	250	—	pF	$V_{GS}=0V$
$C_{oss}$	Output Capacitance	—	80	—		$V_{DS}=25V$
$C_{rss}$	Reverse Transfer Capacitance	—	15	—		$f=1.0\text{MHz}$ See Figure 5

## Source-Drain Ratings and Characteristics

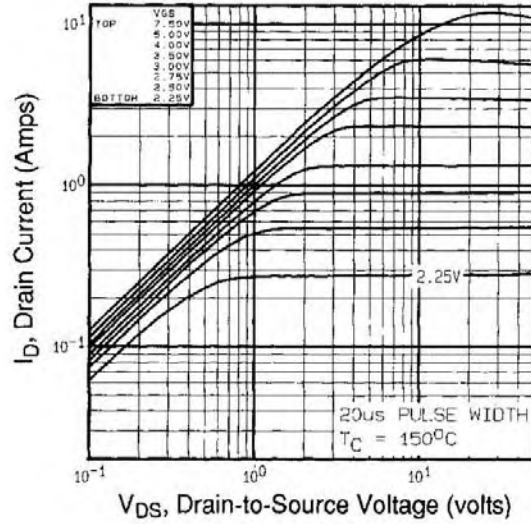
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	4.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	17		
$V_{SD}$	Diode Forward Voltage	—	—	2.5	V	$T_J=25^\circ\text{C}, I_S=4.3A, V_{GS}=0V$ ④
$t_{rr}$	Reverse Recovery Time	—	100	130	ns	$T_J=25^\circ\text{C}, I_F=5.6A$
$Q_{rr}$	Reverse Recovery Charge	—	0.50	0.65	$\mu C$	$di/dt=100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

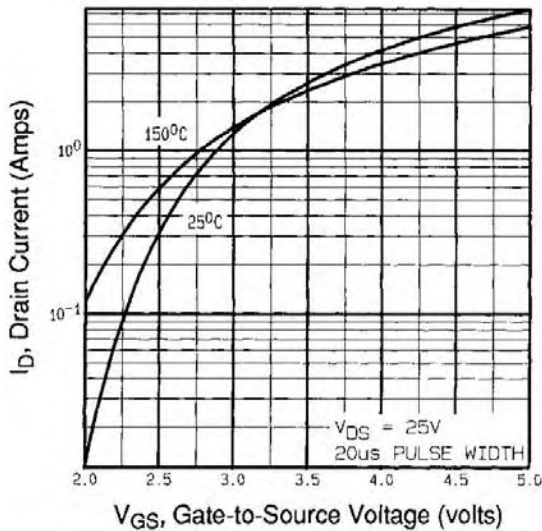
- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ②  $V_{DD}=25V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=8.1\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=4.3A$  (See Figure 12)
- ③  $I_{SD}\leq 5.6A$ ,  $di/dt\leq 140A/\mu s$ ,  $V_{DD}\leq V_{(BR)DSS}$ ,  $T_J\leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



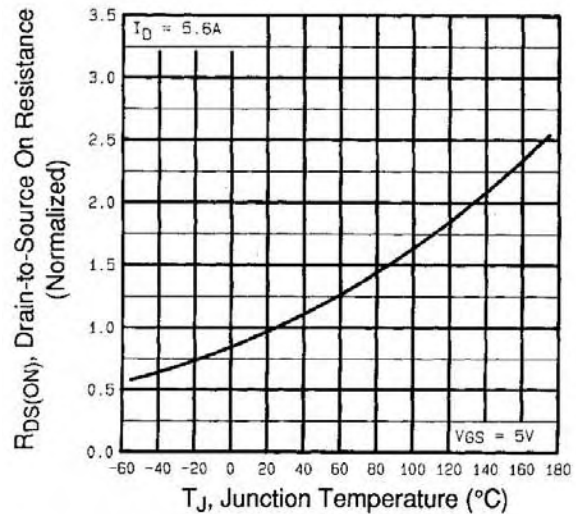
**Fig 1.** Typical Output Characteristics,  $T_C=25^\circ\text{C}$



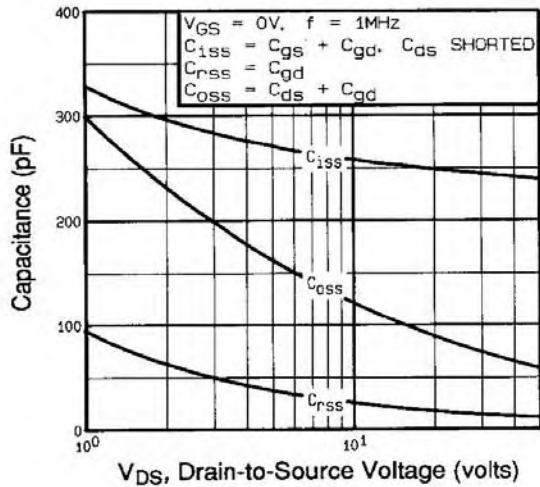
**Fig 2.** Typical Output Characteristics,  $T_C=150^\circ\text{C}$



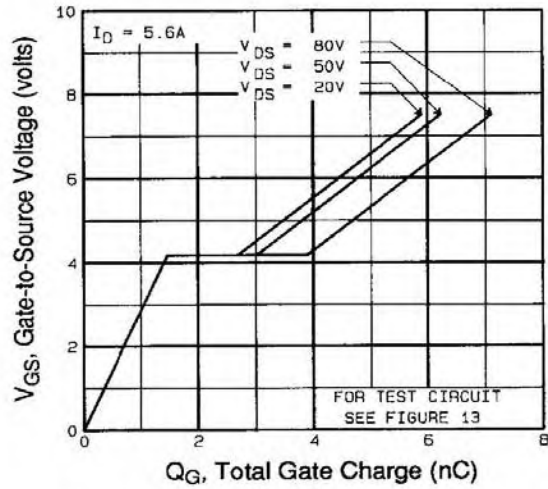
**Fig 3.** Typical Transfer Characteristics



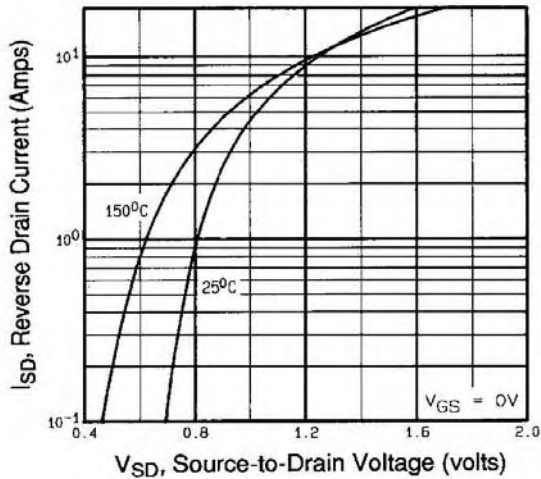
**Fig 4.** Normalized On-Resistance Vs. Temperature



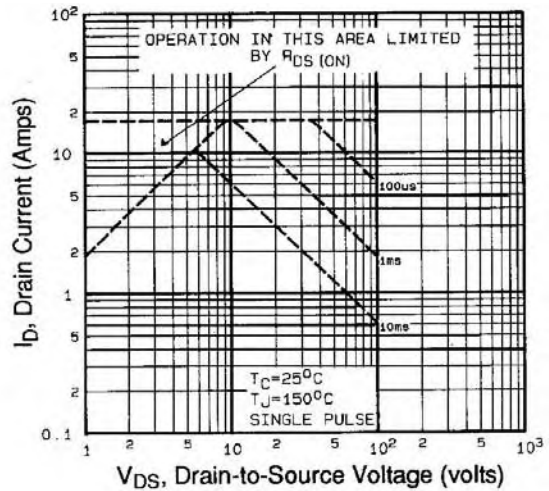
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



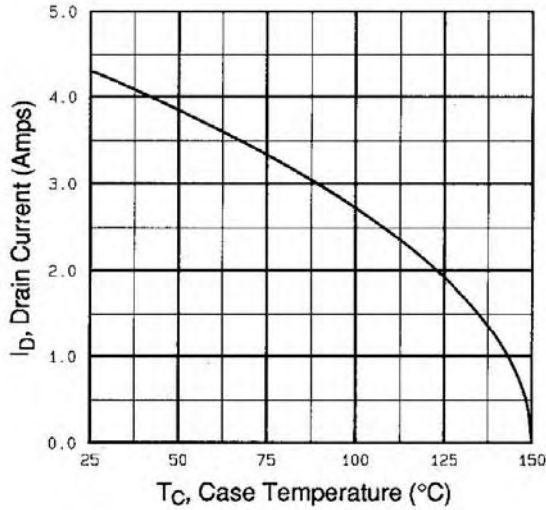
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



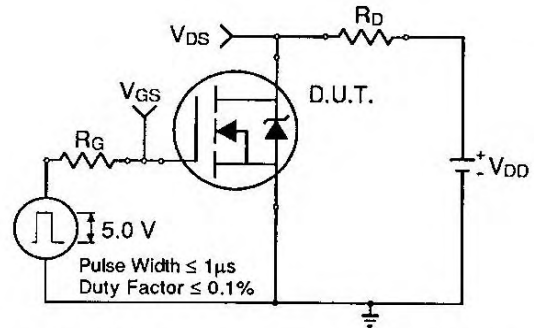
**Fig 7.** Typical Source-Drain Diode Forward Voltage



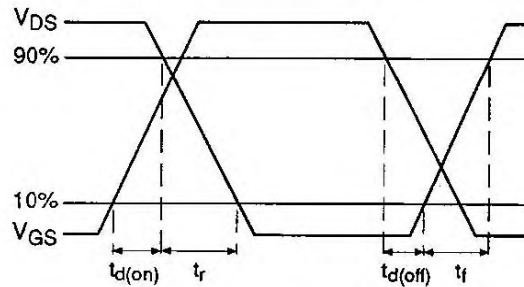
**Fig 8.** Maximum Safe Operating Area



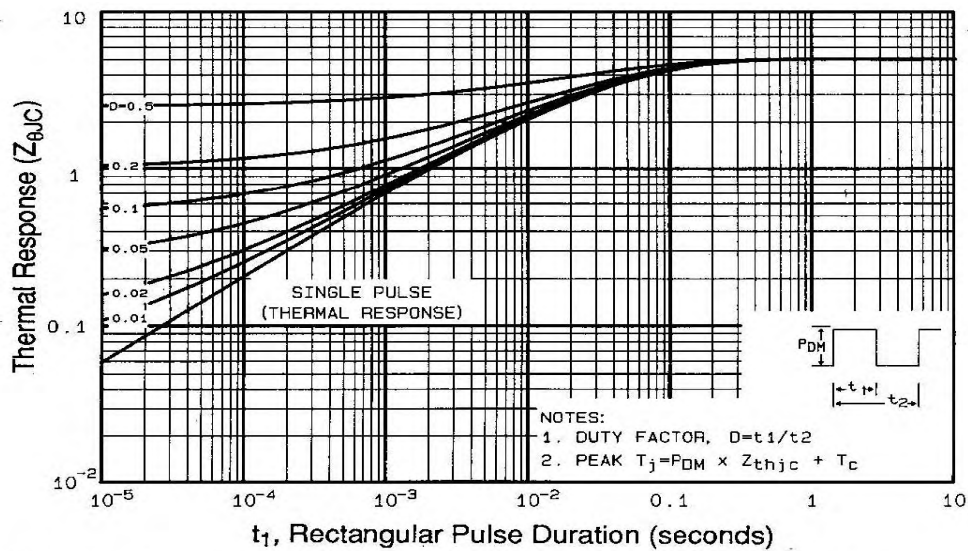
**Fig 9.** Maximum Drain Current Vs. Case Temperature



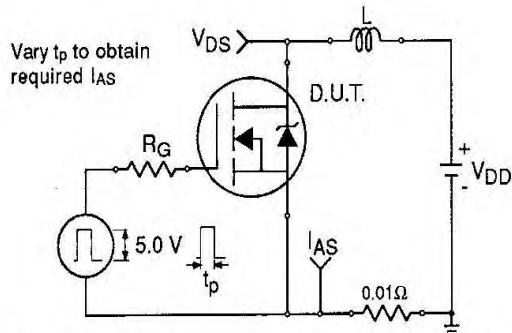
**Fig 10a.** Switching Time Test Circuit



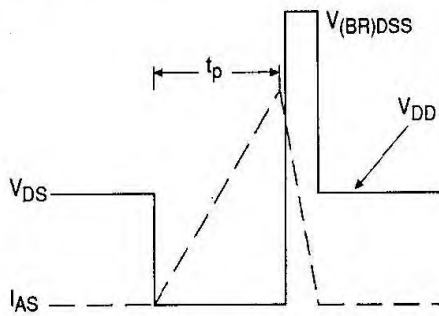
**Fig 10b.** Switching Time Waveforms



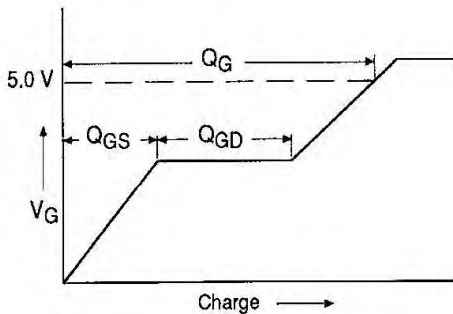
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case  
www.irf.com



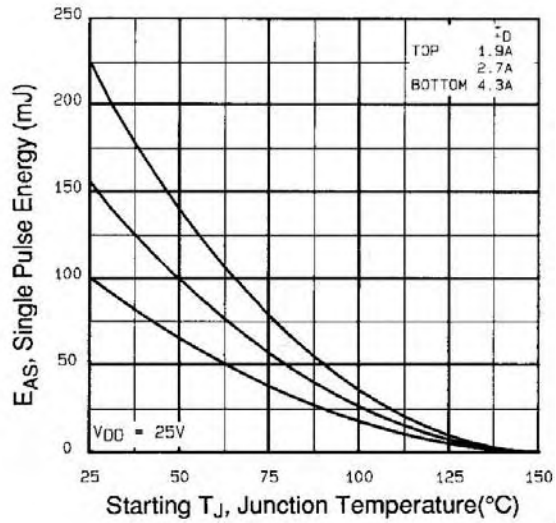
**Fig 12a.** Unclamped Inductive Test Circuit



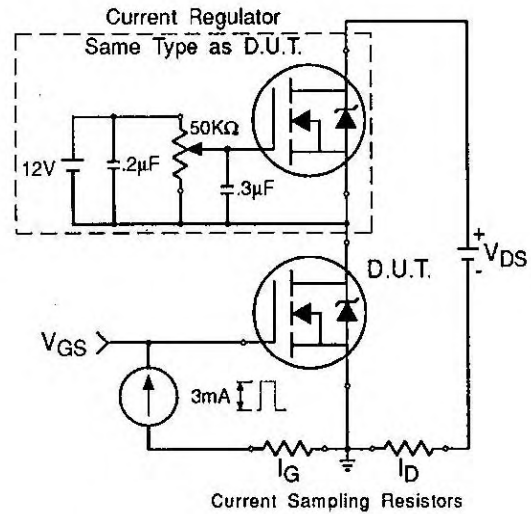
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

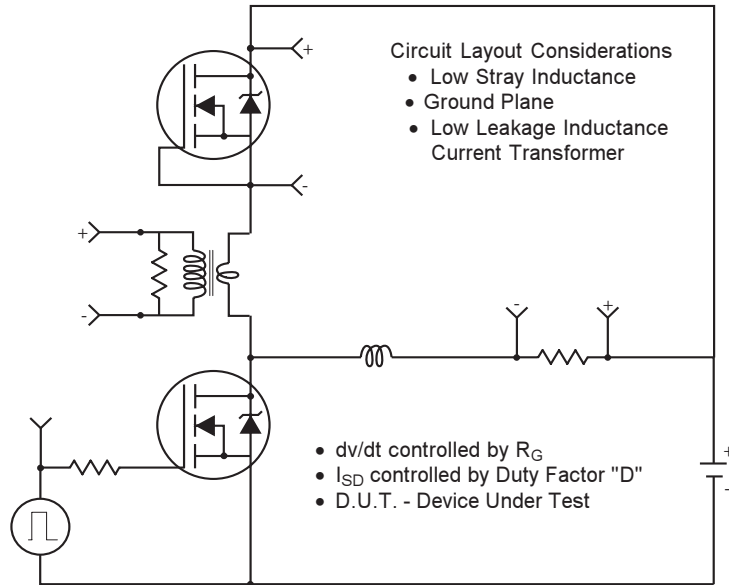


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



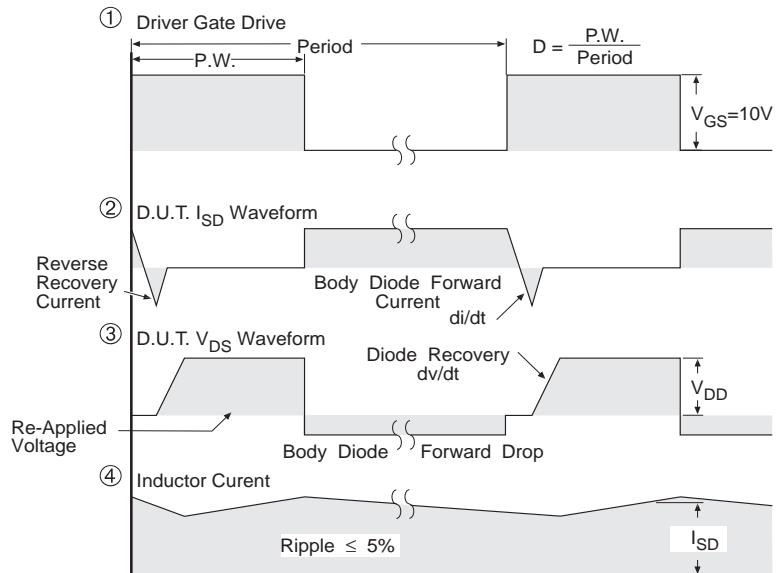
**Fig 13b.** Gate Charge Test Circuit  
www.irf.com

**Peak Diode Recovery dv/dt Test Circuit**



\* Reverse Polarity for P-Channel

\*\* Use P-Channel Driver for P-Channel Measurements



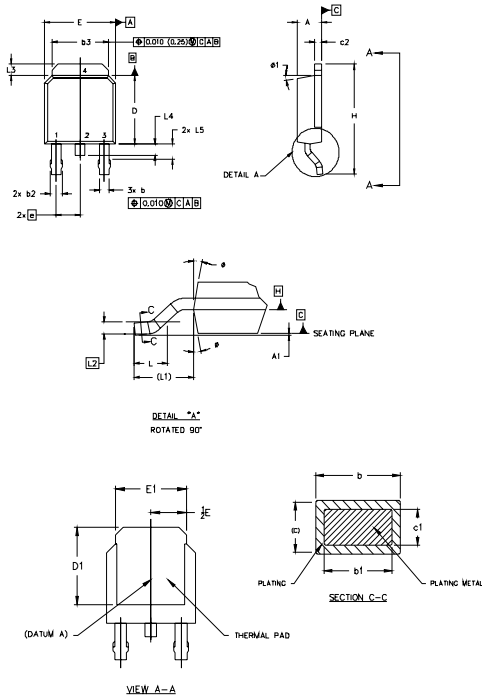
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig. 14** For N Channel HEXFETS

# IRLR/U110PbF

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
  - 3.0 LEAD DIMENSION UNCONTROLLED IN L5
  - 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
  - 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH; MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.29	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.036	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.48	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.048	0.09	.018	.036	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.75	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090	BSC	
H	8.40	10.41	.330	.410	
L	1.40	1.78	.055	.070	
L1	2.74	REF.	.108	REF.	
L2	0.651	BSC	.026	BSC	
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

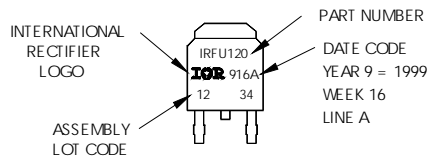
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

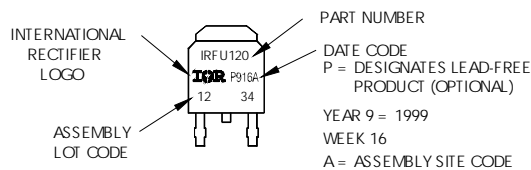
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
indicates "Lead-Free"



OR





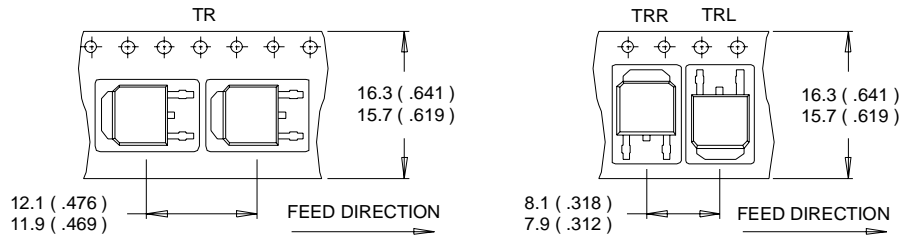


# IRLR/U110PbF

International  
**IR** Rectifier

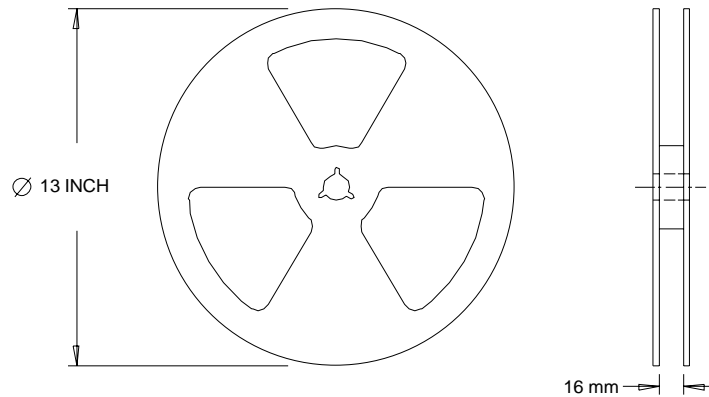
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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